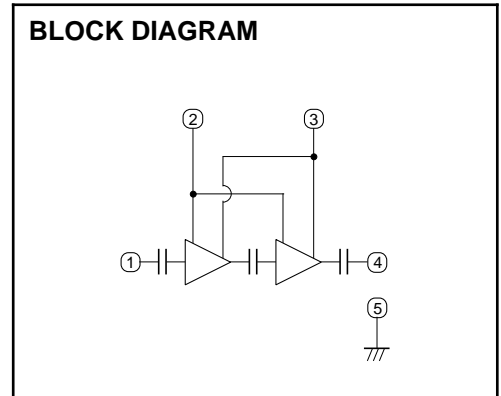
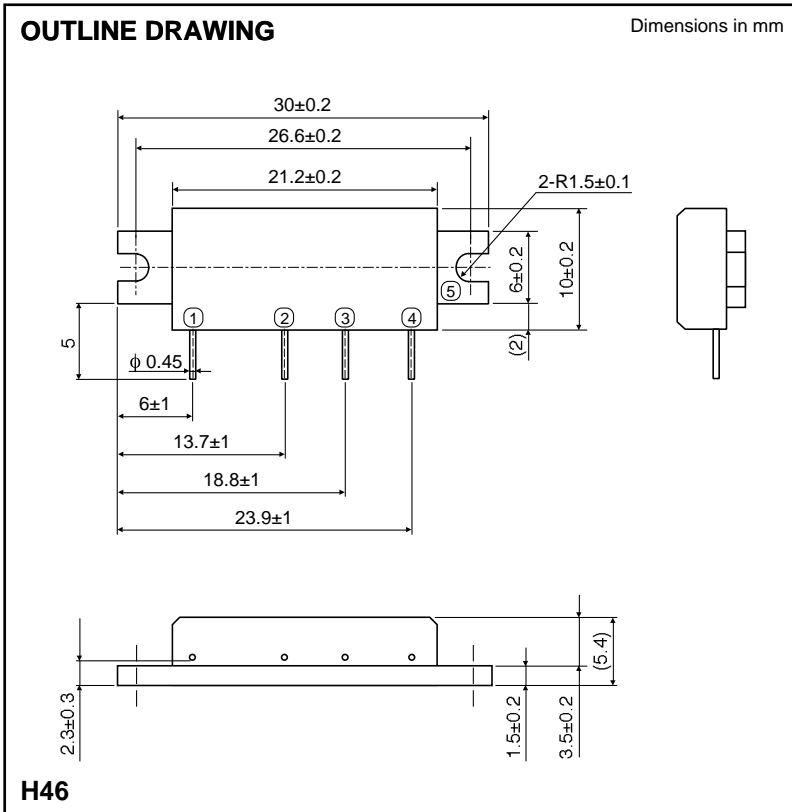


MITSUBISHI RF POWER MODULE
M68757L

SILICON MOS FET POWER AMPLIFIER, 806-870MHz, 3W, FM PORTABLE RADIO



- PIN:
 ①Pin : RF INPUT
 ②VGG : GATE BIAS SUPPLY
 ③VDD : DRAIN BIAS SUPPLY
 ④PO : RF OUTPUT
 ⑤GND: FIN

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VDD	Supply voltage	VGG 3.5V, ZG=ZL=50	9.2	V
VGG	Gate bias voltage		4	V
Pin	Input power	f=806-870MHz, ZG=ZL=50	70	mW
Po	Output power	f=806-870MHz, ZG=ZL=50	5	W
Tc (OP)	Operation case temperature	f=806-870MHz, ZG=ZL=50	-30 to +100	°C
Tstg	Storage temperature		-40 to +100	°C

Note. Above parameters are guaranteed independently.

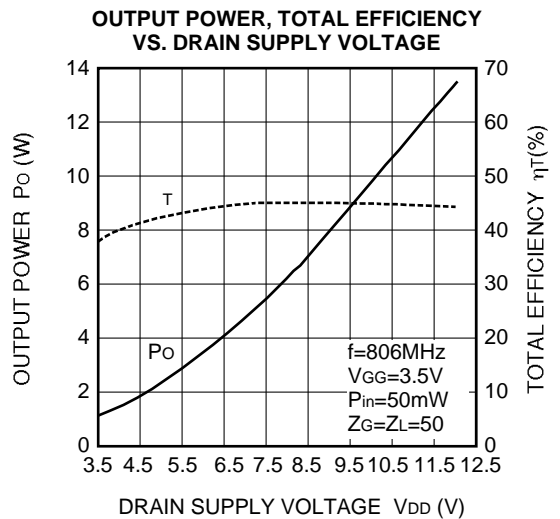
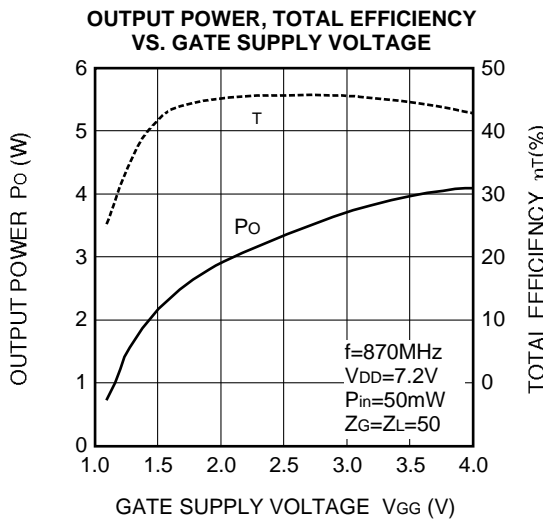
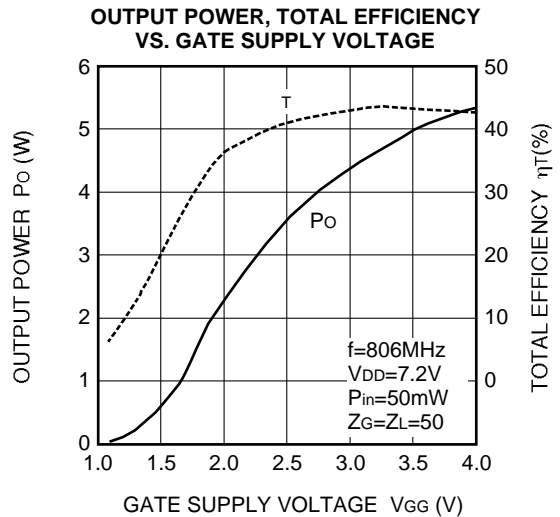
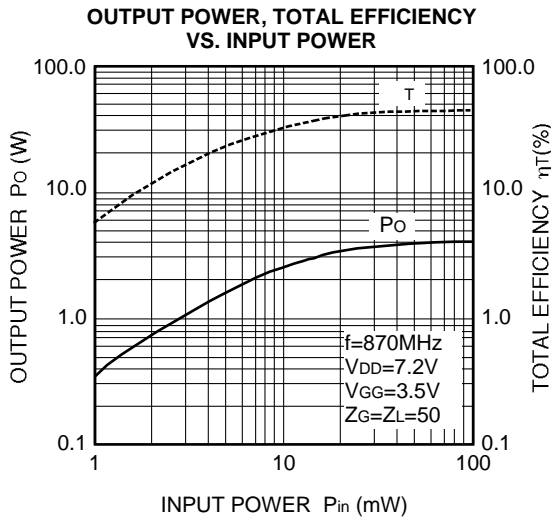
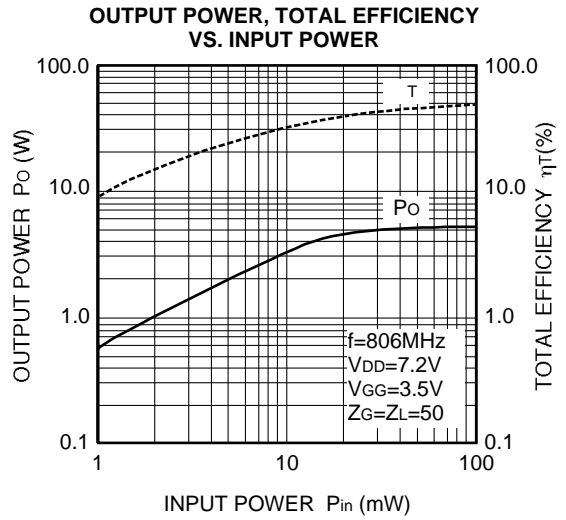
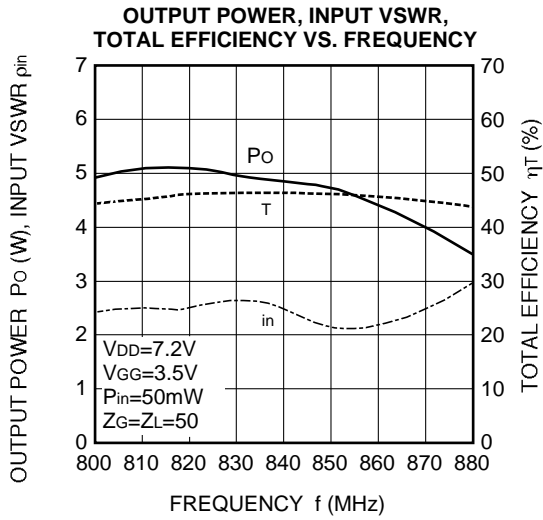
ELECTRICAL CHARACTERISTICS (Tc=25°C, ZG=ZL=50 unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		806	870	MHz
Po	Output power		3		W
T	Total efficiency	VDD=7.2V, VGG=3.5V, Pin=50mW	30		%
2fo	2nd. harmonic			-28	dBc
in	Input VSWR			4	—
—	Stability	ZG=ZL=50, VDD=5-9.2V, Load VSWR <4:1	No parasitic oscillation		—
—	Load VSWR tolerance	VDD=9V, Pin=50mW, Po=3W (VGG Adjust), ZL=20:1	No degradation or destroy		—

Note. Above parameters, ratings, limits and test conditions are subject to change.

SILICON MOS FET POWER AMPLIFIER, 806-870MHz, 3W, FM PORTABLE RADIO

TYPICAL PERFORMANCE DATA



SILICON MOS FET POWER AMPLIFIER, 806-870MHz, 3W, FM PORTABLE RADIO

